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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Obsolete
Core Processor	PIC
Core Size	8-Bit
Speed	25MHz
Connectivity	I ² C, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, HLVD, POR, PWM, WDT
Number of I/O	36
Program Memory Size	64KB (32K x 16)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	3.8K x 8
Voltage - Supply (Vcc/Vdd)	4.2V ~ 5.5V
Data Converters	A/D 13x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	44-TQFP
Supplier Device Package	44-TQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/pic18f4610-e-pt

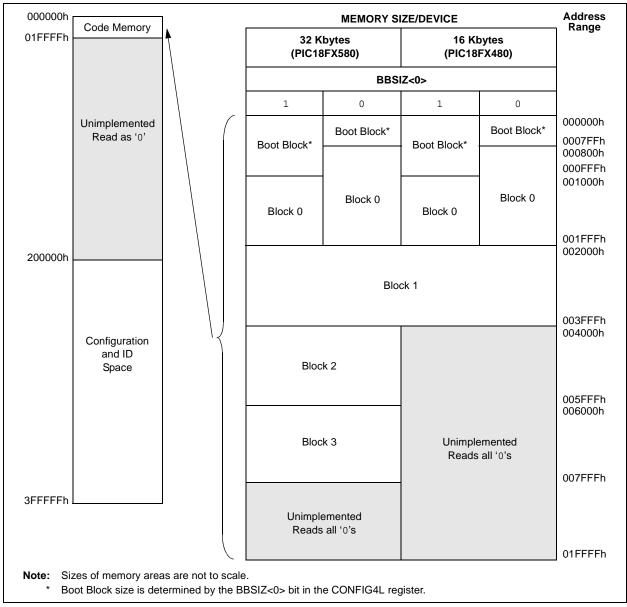
Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

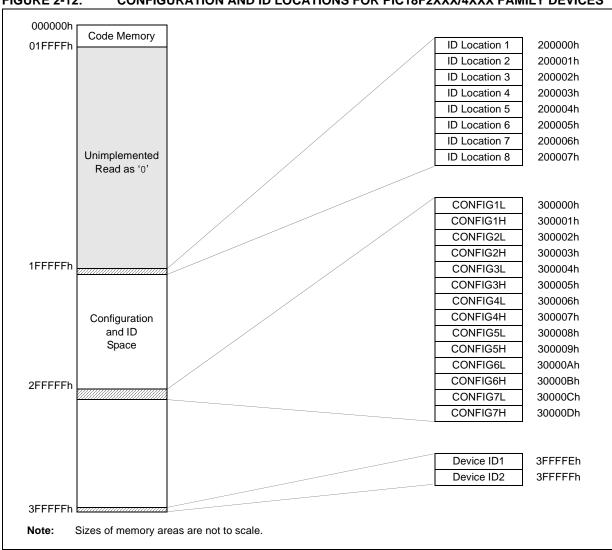
TABLE 2-6:IMPLEMENTATION OF CODE MEMORY

Device	Code Memory Size (Bytes)
PIC18F2480	
PIC18F4480	000000h-003FFFh (16K)
PIC18F2580	000000h 007EEEh (22K)
PIC18F4580	000000h-007FFFh (32K)

FIGURE 2-10: MEMORY MAP AND THE CODE MEMORY SPACE FOR PIC18F2480/2580/4480/4580 DEVICES



For PIC18F2221/4221 devices, the code memory space extends from 0000h to 00FFFh (4 Kbytes) in one 4-Kbyte block. For PIC18F2321/4321 devices, the code memory space extends from 0000h to 01FFFh (8 Kbytes) in two 4-Kbyte blocks. Addresses, 0000h through 07FFh, however, define a variable "Boot Block" region that is treated separately from Block 0. All of these blocks define code protection boundaries within the code memory space.



2.5 Entering and Exiting High-Voltage ICSP Program/Verify Mode

As shown in <u>Figure 2-14</u>, the High-Voltage ICSP Program/Verify mode is entered by holding PGC and PGD low and then raising MCLR/VPP/RE3 to VIHH (high voltage). Once in this mode, the code memory, data EEPROM (selected devices only, see **Section 3.3 "Data EEPROM Programming"**), ID locations and Configuration bits can be accessed and programmed in serial fashion. Figure 2-15 shows the exit sequence.

The sequence that enters the device into the Program/Verify mode places all unused I/Os in the high-impedance state.

FIGURE 2-14: ENTERING HIGH-VOLTAGE PROGRAM/VERIFY MODE

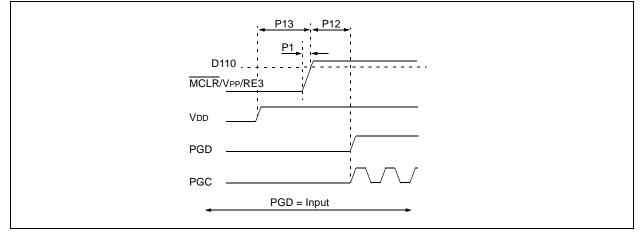
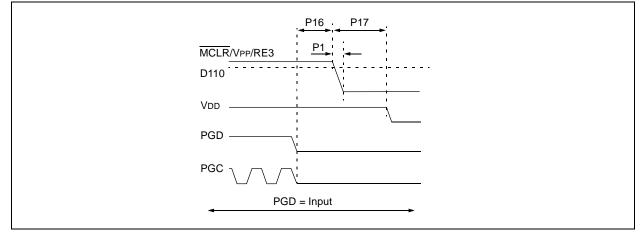


FIGURE 2-15: EXITING HIGH-VOLTAGE PROGRAM/VERIFY MODE



2.6 Entering and Exiting Low-Voltage ICSP Program/Verify Mode

When the LVP Configuration bit is '1' (see Section 5.3 "Single-Supply ICSP Programming"), the Low-Voltage ICSP mode is enabled. As shown in Figure 2-16, Low-Voltage ICSP Program/Verify mode is entered by holding PGC and PGD low, placing a logic high on PGM and then raising MCLR/VPP/RE3 to VIH. In this mode, the RB5/PGM pin is dedicated to the programming function and ceases to be a general purpose I/O pin. Figure 2-17 shows the exit sequence.

The sequence that enters the device into the Program/Verify mode places all unused I/Os in the high-impedance state.

FIGURE 2-16: ENTERING LOW-VOLTAGE PROGRAM/VERIFY MODE

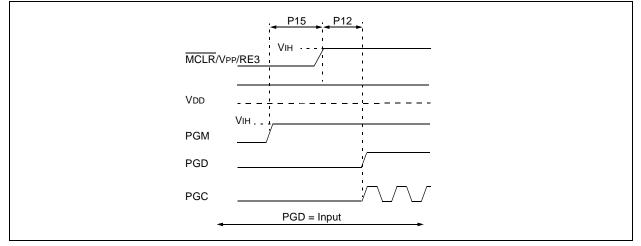
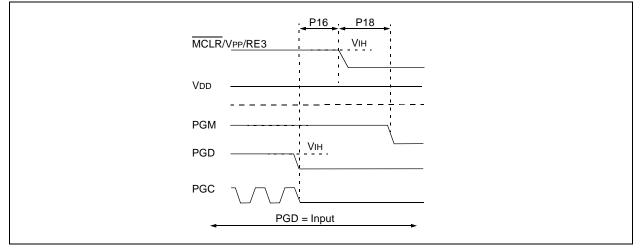


FIGURE 2-17: EXITING LOW-VOLTAGE PROGRAM/VERIFY MODE



2.7 Serial Program/Verify Operation

The PGC pin is used as a clock input pin and the PGD pin is used for entering command bits and data input/output during serial operation. Commands and data are transmitted on the rising edge of PGC, latched on the falling edge of PGC and are Least Significant bit (LSb) first.

2.7.1 4-BIT COMMANDS

All instructions are 20 bits, consisting of a leading 4-bit command followed by a 16-bit operand, which depends on the type of command being executed. To input a command, PGC is cycled four times. The commands needed for programming and verification are shown in Table 2-8.

Depending on the 4-bit command, the 16-bit operand represents 16 bits of input data or 8 bits of input data and 8 bits of output data.

Throughout this specification, commands and data are presented as illustrated in Table 2-9. The 4-bit command is shown Most Significant bit (MSb) first. The command operand, or "Data Payload", is shown as <MSB><LSB>. Figure 2-18 demonstrates how to serially present a 20-bit command/operand to the device.

2.7.2 CORE INSTRUCTION

The core instruction passes a 16-bit instruction to the CPU core for execution. This is needed to set up registers as appropriate for use with other commands.

TABLE 2-8: COMMANDS FOR PROGRAMMING

Description	4-Bit Command
Core Instruction (Shift in16-bit instruction)	0000
Shift Out TABLAT Register	0010
Table Read	1000
Table Read, Post-Increment	1001
Table Read, Post-Decrement	1010
Table Read, Pre-Increment	1011
Table Write	1100
Table Write, Post-Increment by 2	1101
Table Write, Start Programming, Post-Increment by 2	1110
Table Write, Start Programming	1111

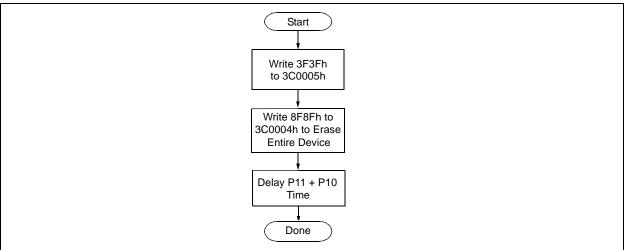
TABLE 2-9: SAMPLE COMMAND SEQUENCE

4-Bit Command	Data Payload	Core Instruction
1101	3C 40	Table Write,
		post-increment by 2

4-Bit Command	Data Payload	Core Instruction
0000	0E 3C	MOVLW 3Ch
0000	6E F8	MOVWF TBLPTRU
0000	0E 00	MOVLW 00h
0000	6E F7	MOVWF TBLPTRH
0000	0E 05	MOVLW 05h
0000	6E F6	MOVWF TBLPTRL
1100	3F 3F	Write 3F3Fh to 3C0005h
0000	0E 3C	MOVLW 3Ch
0000	6E F8	MOVWF TBLPTRU
0000	0E 00	MOVLW 00h
0000	6E F7	MOVWF TBLPTRH
0000	0E 04	MOVLW 04h
0000	6E F6	MOVWF TBLPTRL
1100	8F 8F	Write 8F8Fh TO 3C0004h to erase entire device.
		NOP
		Hold PGD low until erase completes.
0000	00 00	
0000	00 00	

TABLE 3-2: BULK ERASE COMMAND SEQUENCE

FIGURE 3-1: BULK ERASE FLOW



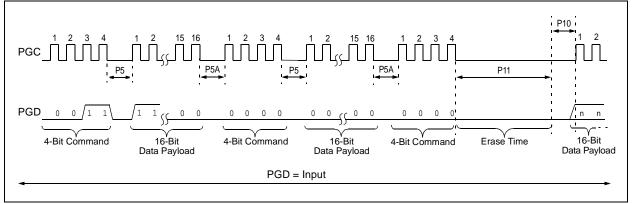
3.1.2 LOW-VOLTAGE ICSP BULK ERASE

When using low-voltage ICSP, the part must be supplied by the voltage specified in Parameter D111 if a Bulk Erase is to be executed. All other Bulk Erase details, as described above, apply.

If it is determined that a program memory erase must be performed at a supply voltage below the Bulk Erase limit, refer to the erase methodology described in Section 3.1.3 "ICSP Row Erase" and Section 3.2.1 "Modifying Code Memory".

If it is determined that a data EEPROM erase (selected devices only, see Section 3.3 "Data EEPROM Programming") must be performed at a supply voltage below the Bulk Erase limit, follow the methodology described in Section 3.3 "Data EEPROM Programming" and write '1's to the array.





3.1.3 ICSP ROW ERASE

Regardless of whether high or low-voltage ICSP is used, it is possible to erase one row (64 bytes of data), provided the block is not code or write-protected. Rows are located at static boundaries, beginning at program memory address, 000000h, extending to the internal program memory limit (see Section 2.3 "Memory Maps").

The Row Erase duration is externally timed and is controlled by PGC. After the WR bit in EECON1 is set, a NOP is issued, where the 4th PGC is held high for the duration of the programming time, P9.

After PGC is brought low, the programming sequence is terminated. PGC must be held low for the time specified by Parameter P10 to allow high-voltage discharge of the memory array.

The code sequence to Row Erase a PIC18F2XXX/4XXX Family device is shown in Table 3-3. The flowchart, shown in Figure 3-3, depicts the logic necessary to completely erase a PIC18F2XXX/4XXX Family device. The timing diagram that details the Start Programming command and Parameters P9 and P10 is shown in Figure 3-5.

Note: The TBLPTR register can point to any byte within the row intended for erase.

3.2 Code Memory Programming

Programming code memory is accomplished by first loading data into the write buffer and then initiating a programming sequence. The write and erase buffer sizes, shown in Table 3-4, can be mapped to any location of the same size, beginning at 000000h. The actual memory write sequence takes the contents of this buffer and programs the proper amount of code memory that contains the Table Pointer.

The programming duration is externally timed and is controlled by PGC. After a Start Programming command is issued (4-bit command, '1111'), a NOP is issued, where the 4th PGC is held high for the duration of the programming time, P9.

After PGC is brought low, the programming sequence is terminated. PGC must be held low for the time specified by Parameter P10 to allow high-voltage discharge of the memory array.

The code sequence to program a PIC18F2XXX/4XXX Family device is shown in Table 3-5. The flowchart, shown in Figure 3-4, depicts the logic necessary to completely write a PIC18F2XXX/4XXX Family device. The timing diagram that details the Start Programming command and Parameters P9 and P10 is shown in Figure 3-5.

Note: The TBLPTR register must point to the same region when initiating the programming sequence as it did when the write buffers were loaded.

TABLE 3-4: WRITE AND ERASE BUFFER SIZES

Devices (Arranged by Family)	Write Buffer Size (Bytes)	Erase Buffer Size (Bytes)	
PIC18F2221, PIC18F2321, PIC18F4221, PIC18F4321	8	64	
PIC18F2450, PIC18F4450	16	64	
PIC18F2410, PIC18F2510, PIC18F4410, PIC18F4510			
PIC18F2420, PIC18F2520, PIC18F4420, PIC18F4520			
PIC18F2423, PIC18F2523, PIC18F4423, PIC18F4523	32	64	
PIC18F2480, PIC18F2580, PIC18F4480, PIC18F4580		64	
PIC18F2455, PIC18F2550, PIC18F4455, PIC18F4550			
PIC18F2458, PIC18F2553, PIC18F4458, PIC18F4553			
PIC18F2515, PIC18F2610, PIC18F4515, PIC18F4610			
PIC18F2525, PIC18F2620, PIC18F4525, PIC18F4620	64	64	
PIC18F2585, PIC18F2680, PIC18F4585, PIC18F4680	- 64		
PIC18F2682, PIC18F2685, PIC18F4682, PIC18F4685			

3.2.1 MODIFYING CODE MEMORY

The previous programming example assumed that the device had been Bulk Erased prior to programming (see **Section 3.1.1 "High-Voltage ICSP Bulk Erase**"). It may be the case, however, that the user wishes to modify only a section of an already programmed device.

The appropriate number of bytes required for the erase buffer must be read out of code memory (as described in Section 4.2 "Verify Code Memory and ID Locations") and buffered. Modifications can be made on this buffer. Then, the block of code memory that was read out must be erased and rewritten with the modified data.

The WREN bit must be set if the WR bit in EECON1 is used to initiate a write sequence.

4-Bit Command	Data Payload	Core Instruction
Step 1: Direct ac	ccess to code memory.	
Step 2: Read an	d modify code memory (see S	ection 4.1 "Read Code Memory, ID Locations and Configuration Bits").
0000	8E A6	BSF EECON1, EEPGD
0000	9C A6	BCF EECON1, CFGS
Step 3: Set the T	Table Pointer for the block to b	e erased.
0000	0E <addr[21:16]></addr[21:16]>	MOVLW <addr[21:16]></addr[21:16]>
0000	6E F8	MOVWF TBLPTRU
0000	0E <addr[8:15]></addr[8:15]>	MOVLW <addr[8:15]></addr[8:15]>
0000	6E F7	MOVWF TBLPTRH
0000	OE <addr[7:0]></addr[7:0]>	MOVLW <addr[7:0]></addr[7:0]>
0000	6E F6	MOVWF TBLPTRL
Step 4: Enable r	nemory writes and set up an e	rase.
0000	84 A6	BSF EECON1, WREN
0000	88 A6	BSF EECON1, FREE
Step 5: Initiate e	rase.	
0000	82 A6	BSF EECON1, WR
0000	00 00	NOP - hold PGC high for time P9 and low for time P10.
Step 6: Load wri	te buffer. The correct bytes wi	Il be selected based on the Table Pointer.
0000	0E <addr[21:16]></addr[21:16]>	MOVLW <addr[21:16]></addr[21:16]>
0000	6E F8	MOVWF TBLPTRU
0000	0E <addr[8:15]></addr[8:15]>	MOVLW <addr[8:15]></addr[8:15]>
0000	6E F7	MOVWF TBLPTRH
0000	0E <addr[7:0]></addr[7:0]>	MOVLW <addr[7:0]></addr[7:0]>
0000	6E F6	MOVWF TBLPTRL
1101	<msb><lsb></lsb></msb>	Write 2 bytes and post-increment address by 2.
•		Repeat as many times as necessary to fill the write buffer
1111	<msb><lsb></lsb></msb>	Write 2 bytes and start programming.
0000	00 00	NOP - hold PGC high for time P9 and low for time P10.
	at each iteration of the loop. T	bugh 6, where the Address Pointer is incremented by the appropriate number of byte he write cycle must be repeated enough times to completely rewrite the contents of
Step 7: Disable	writes.	
0000	94 A6	BCF EECON1, WREN

TABLE 3-6: MODIFYING CODE MEMORY

3.3 Data EEPROM Programming

Note: Data EEPROM programming is not available on the following devices:			
PIC18F2410	PIC18F4410		
PIC18F2450	PIC18F4450		
PIC18F2510	PIC18F4510		
PIC18F2515	PIC18F4515		
PIC18F2610	PIC18F4610		

Data EEPROM is accessed one byte at a time via an Address Pointer (register pair: EEADRH:EEADR) and a data latch (EEDATA). Data EEPROM is written by loading EEADRH:EEADR with the desired memory location, EEDATA, with the data to be written and initiating a memory write by appropriately configuring the EECON1 register. A byte write automatically erases the location and writes the new data (erase-before-write).

When using the EECON1 register to perform a data EEPROM write, both the EEPGD and CFGS bits must be cleared (EECON1<7:6> = 00). The WREN bit must be set (EECON1<2> = 1) to enable writes of any sort and this must be done prior to initiating a write sequence. The write sequence is initiated by setting the WR bit (EECON1<1> = 1).

The write begins on the falling edge of the 4th PGC after the WR bit is set. It ends when the WR bit is cleared by hardware.

After the programming sequence terminates, PGC must still be held low for the time specified by Parameter P10 to allow high-voltage discharge of the memory array.

FIGURE 3-6: PROGRAM DATA FLOW

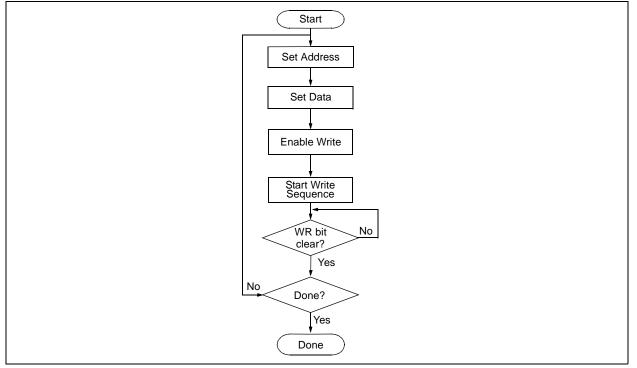
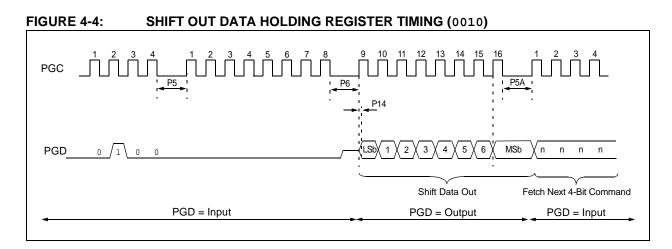


TABLE 3-7: PROGRAMMING DATA MEMORY

4-Bit Command	Data Payload	Core Instruction			
Step 1: Direct acc					
0000 0000	9E A6 9C A6	BCF EECON1, EEPGD BCF EECON1, CFGS			
Step 2: Set the da	ata EEPROM Address Pointe	er.			
0000 0000 0000 0000	OE <addr> 6E A9 OE <addrh> 6E AA</addrh></addr>	MOVLW <addr> MOVWF EEADR MOVLW <addrh> MOVWF EEADRH</addrh></addr>			
Step 3: Load the	data to be written.				
0000 0000	OE <data> 6E A8</data>	MOVLW <data> MOVWF EEDATA</data>			
Step 4: Enable m	emory writes.				
0000	84 A6	BSF EECON1, WREN			
Step 5: Initiate wi	rite.				
0000	82 A6	BSF EECON1, WR			
Step 6: Poll WR b	pit, repeat until the bit is clear	r.			
0000 0000 0000 0010	50 A6 6E F5 00 00 <msb><lsb></lsb></msb>	MOVF EECON1, W, O MOVWF TABLAT NOP Shift out data ⁽¹⁾			
Step 7: Hold PGC low for time P10.					
Step 8: Disable w	vrites.				
0000	94 A6	BCF EECON1, WREN			
Repeat Steps 2 th	Repeat Steps 2 through 8 to write more data.				

Note 1: See Figure 4-4 for details on shift out data timing.



4.5 Verify Data EEPROM

A data EEPROM address may be read via a sequence of core instructions (4-bit command, '0000') and then output on PGD via the 4-bit command, '0010' (TABLAT register). The result may then be immediately compared to the appropriate data in the programmer's memory for verification. Refer to **Section 4.4** "**Read Data EEPROM Memory**" for implementation details of reading data EEPROM.

4.6 Blank Check

The term Blank Check means to verify that the device has no programmed memory cells. All memories must be verified: code memory, data EEPROM, ID locations and Configuration bits. The Device ID registers (3FFFFEh:3FFFFh) should be ignored.

A "blank" or "erased" memory cell will read as '1'. Therefore, Blank Checking a device merely means to verify that all bytes read as FFh, except the Configuration bits. Unused (reserved) Configuration bits will read '0' (programmed). Refer to Figure 4-5 for blank configuration expect data for the various PIC18F2XXX/4XXX Family devices.

Given that Blank Checking is merely code and data EEPROM verification with FFh expect data, refer to Section 4.4 "Read Data EEPROM Memory" and Section 4.2 "Verify Code Memory and ID Locations" for implementation details.



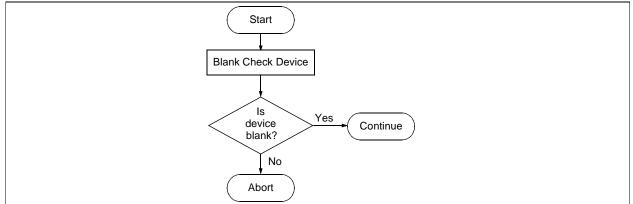


TABLE 5-1: CONFIGURATION BITS AND DEVICE IDS

File 1	Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	Default/ Unprogrammed Value														
300000h ^(1,8)	CONFIG1L		_	USBDIV	CPUDIV1	CPUDIV0	PLLDIV2	PLLDIV1	PLLDIV0	00 0000														
300001h	CONFIG1H	IESO	FCMEN		_	FOSC3	FOSC2	FOSC1	FOSC0	00 0111														
30000111	CONTONT	1200	TOWEN			10000	10002	10001	10000	00 0101 ^(1,8)														
300002h	CONFIG2L			_	BORV1	BORV0	BOREN1	BOREN0	PWRTEN	1 1111														
30000211				VREGEN ^(1,8)	BORVI	BORVU	BORLINI	BORLINU	FWINILIN	01 1111 (1,8)														
300003h	CONFIG2H	—	—	_	WDTPS3	WDTPS2	WDTPS1	WDTPS0	WDTEN	1 1111														
300005h	CONFIG3H	MCLRE	_	_	_	_	LPT1OSC	PBADEN	CCP2MX ⁽⁷⁾	1011 (7)														
00000011		MOEINE					LI I I OOO	TBREEN	—	101-														
		DEBUG	DEBUG		ICPRT ⁽¹⁾	—	_				1001-1 ⁽¹⁾													
				DEBUG	DEBUG	DEBUG		BBSIZ1	BBSIZ0	_				1000 -1-1										
300006h	CONFIG4L						DEBUG	DEBUG	DEBUG	DEBUG	DEBUG	DEBUG	DEBUG	DEBUG	DEBUG	DEBUG	XINST	_	BBSIZ ⁽³⁾	_	LVP	—	STVREN	10-0 -1-1 (3)
													ICPRT ⁽⁸⁾	—	BBSIZ ⁽⁸⁾				100- 01-1 ⁽⁸⁾					
				BBSIZ1 ⁽²⁾	BBSIZ2(2)	-				1000 -1-1 (2)														
300008h	CONFIG5L	_	—	CP5 ⁽¹⁰⁾	CP4 ⁽⁹⁾	CP3 ⁽⁴⁾	CP2 ⁽⁴⁾	CP1	CP0	11 1111														
300009h	CONFIG5H	CPD	CPB	_	—	-	—	-	—	11														
30000Ah	CONFIG6L	_	—	WRT5 ⁽¹⁰⁾	WRT4 ⁽⁹⁾	WRT3 ⁽⁴⁾	WRT2 ⁽⁴⁾	WRT1	WRT0	11 1111														
30000Bh	CONFIG6H	WRTD	WRTB	WRTC ⁽⁵⁾	—		_		—	111														
30000Ch	CONFIG7L		_	EBTR5 ⁽¹⁰⁾	EBTR4 ⁽⁹⁾	EBTR3 ⁽⁴⁾	EBTR2 ⁽⁴⁾	EBTR1	EBTR0	11 1111														
30000Dh	CONFIG7H		EBTRB		_		_		_	-1														
3FFFFEh	DEVID1 ⁽⁶⁾	DEV2	DEV1	DEV0	REV4	REV3	REV2	REV1	REV0	See Table 5-2														
3FFFFFh	DEVID2 ⁽⁶⁾	DEV10	DEV9	DEV8	DEV7	DEV6	DEV5	DEV4	DEV3	See Table 5-2														

Legend: -= unimplemented. Shaded cells are unimplemented, read as '0'.

Note 1: Implemented only on PIC18F2455/2550/4455/4550 and PIC18F2458/2553/4458/4553 devices.

2: Implemented on PIC18F2585/2680/4585/4680, PIC18F2682/2685 and PIC18F4682/4685 devices only.

3: Implemented on PIC18F2480/2580/4480/4580 devices only.

4: These bits are only implemented on specific devices based on available memory. Refer to Section 2.3 "Memory Maps".

5: In PIC18F2480/2580/4480/4580 devices, this bit is read-only in Normal Execution mode; it can be written only in Program mode.

6: DEVID registers are read-only and cannot be programmed by the user.

7: Implemented on all devices with the exception of the PIC18FXX8X and PIC18F2450/4450 devices.

8: Implemented on PIC18F2450/4450 devices only.

9: Implemented on PIC18F2682/2685 and PIC18F4682/4685 devices only.

10: Implemented on PIC18F2685/4685 devices only.

TABLE 5-2: DEVICE ID VALUES (CONTINUED)

Device	Device ID Value				
Device	DEVID2	DEVID1			
PIC18F4585	0Eh	101x xxxx			
PIC18F4610	0Ch	001x xxxx			
PIC18F4620	0Ch	000x xxxx			
PIC18F4680	0Eh	100x xxxx			
PIC18F4682	27h	010x xxxx			
PIC18F4685	27h	011x xxxx			

Legend: The 'x's in DEVID1 contain the device revision code.

Note 1: DEVID1 bit 4 is used to determine the device type (REV4 = 0).

2: DEVID1 bit 4 is used to determine the device type (REV4 = 1).

TABLE 5-3: PIC18F2XXX/4XXX FAMILY BIT DESCRIPTIONS (CONTINUED)

Bit Name	Configuration Words	Description
PLLDIV<2:0>	CONFIG1L	Oscillator Selection bits (PIC18F2455/2550/4455/4550, PIC18F2458/2553/4458/4553 and PIC18F2450/4450 devices only)
		Divider must be selected to provide a 4 MHz input into the 96 MHz PLL: 111 = Oscillator divided by 12 (48 MHz input) 110 = Oscillator divided by 10 (40 MHz input) 101 = Oscillator divided by 6 (24 MHz input) 100 = Oscillator divided by 5 (20 MHz input) 011 = Oscillator divided by 4 (16 MHz input) 010 = Oscillator divided by 3 (12 MHz input) 001 = Oscillator divided by 2 (8 MHz input) 000 = No divide – oscillator used directly (4 MHz input)
VREGEN	CONFIG2L	USB Voltage Regulator Enable bit (PIC18F2455/2550/4455/4550, PIC18F2458/2553/4458/4553 and PIC18F2450/4450 devices only) 1 = USB voltage regulator is enabled
BORV<1:0>	CONFIG2L	0 = USB voltage regulator is disabled Brown-out Reset Voltage bits 11 = VBOR is set to 2.0V 10 = VBOR is set to 2.7V 01 = VBOR is set to 4.2V 00 = VBOR is set to 4.5V
BOREN<1:0>	CONFIG2L	 Brown-out Reset Enable bits 11 = Brown-out Reset is enabled in hardware only (SBOREN is disabled) 10 = Brown-out Reset is enabled in hardware only and disabled in Sleep mode SBOREN is disabled) 01 = Brown-out Reset is enabled and controlled by software (SBOREN is enabled) 00 = Brown-out Reset is disabled in hardware and software
PWRTEN	CONFIG2L	Power-up Timer Enable bit 1 = PWRT is disabled 0 = PWRT is enabled
WDPS<3:0>	CONFIG2H	Watchdog Timer Postscaler Select bits 1111 = 1:32,768 1110 = 1:16,384 1101 = 1:8,192 1100 = 1:4,096 1011 = 1:2,048 1010 = 1:1,024 1001 = 1:512 1000 = 1:256 0111 = 1:128 0110 = 1:64 0101 = 1:32 0100 = 1:16 0011 = 1:8 0010 = 1:4 0001 = 1:2
		0000 = 1:1 000 = 1:1

Note 1: The BBSIZ bits, BBSIZ<1:0> and BBSIZ<2:1> bits, cannot be changed once any of the following code-protect bits are enabled: CPB or CP0, WRTB or WRT0, EBTRB or EBTR0.

2: Not available in PIC18FXX8X and PIC18F2450/4450 devices.

Bit Name	Configuration Words	Description					
WRT5	CONFIG6L	Write Protection bit (Block 5 code memory area) (PIC18F2685 and PIC18F4685 devices only)					
		1 = Block 5 is not write-protected0 = Block 5 is write-protected					
WRT4	CONFIG6L	Write Protection bit (Block 4 code memory area) (PIC18F2682/2685 and PIC18F4682/4685 devices only)					
		1 = Block 4 is not write-protected0 = Block 4 is write-protected					
WRT3	CONFIG6L	Write Protection bit (Block 3 code memory area)					
		1 = Block 3 is not write-protected					
		0 = Block 3 is write-protected					
WRT2	CONFIG6L	Write Protection bit (Block 2 code memory area)					
		1 = Block 2 is not write-protected0 = Block 2 is write-protected					
WRT1	CONFIG6L	Write Protection bit (Block 1 code memory area)					
		1 = Block 1 is not write-protected0 = Block 1 is write-protected					
WRT0	CONFIG6L	Write Protection bit (Block 0 code memory area)					
		1 = Block 0 is not write-protected					
		0 = Block 0 is write-protected					
WRTD	CONFIG6H	Write Protection bit (Data EEPROM)					
		 1 = Data EEPROM is not write-protected 0 = Data EEPROM is write-protected 					
WRTB	CONFIG6H	Write Protection bit (Boot Block memory area)					
		1 = Boot Block is not write-protected					
		0 = Boot Block is write-protected					
WRTC	CONFIG6H	Write Protection bit (Configuration registers)					
		1 = Configuration registers are not write-protected					
		0 = Configuration registers are write-protected					
EBTR5	CONFIG7L	Table Read Protection bit (Block 5 code memory area) (PIC18F2685 and PIC18F4685 devices only)					
		 1 = Block 5 is not protected from Table Reads executed in other blocks 0 = Block 5 is protected from Table Reads executed in other blocks 					
EBTR4	CONFIG7L	Table Read Protection bit (Block 4 code memory area) (PIC18F2682/2685 and PIC18F4682/4685 devices only)					
		 1 = Block 4 is not protected from Table Reads executed in other blocks 0 = Block 4 is protected from Table Reads executed in other blocks 					
EBTR3	CONFIG7L	Table Read Protection bit (Block 3 code memory area)					
		 1 = Block 3 is not protected from Table Reads executed in other blocks 0 = Block 3 is protected from Table Reads executed in other blocks 					
EBTR2	CONFIG7L	Table Read Protection bit (Block 2 code memory area)					
		1 = Block 2 is not protected from Table Reads executed in other blocks					
		0 = Block 2 is protected from Table Reads executed in other blocks					
EBTR1	CONFIG7L	Table Read Protection bit (Block 1 code memory area)					
		 1 = Block 1 is not protected from Table Reads executed in other blocks 0 = Block 1 is protected from Table Reads executed in other blocks 					

TABLE 5-3:	PIC18F2XXX/4XXX FAMILY BIT DESCRIPTIONS ((CONTINUED)

Note 1: The BBSIZ bits, BBSIZ<1:0> and BBSIZ<2:1> bits, cannot be changed once any of the following code-protect bits are enabled: CPB or CP0, WRTB or WRT0, EBTRB or EBTR0.

2: Not available in PIC18FXX8X and PIC18F2450/4450 devices.

	•••													
	Configuration Word (CONFIGxx)													
Device	1L	1H	2L	2H	3L	3H	4L	4H	5L	5H	6L	6H	7L	7H
Device	Address (30000xh)													
	0h	1h	2h	3h	4h	5h	6h	7h	8h	9h	Ah	Bh	Ch	Dh
PIC18F4620	00	CF	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40
PIC18F4680	00	CF	1F	1F	00	86	C5	00	0F	C0	0F	E0	0F	40
PIC18F4682	00	CF	1F	1F	00	86	C5	00	3F	C0	3F	E0	3F	40
PIC18F4685	00	CF	1F	1F	00	86	C5	00	3F	C0	3F	E0	3F	40

TABLE 5-5: CONFIGURATION WORD MASKS FOR COMPUTING CHECKSUMS (CONTINUED)

Legend: Shaded cells are unimplemented.

6.0 AC/DC CHARACTERISTICS TIMING REQUIREMENTS FOR PROGRAM/VERIFY TEST MODE

Param No. Sym		Characteristic	Min	Max	Units	Conditions		
D110	Vihh	High-Voltage Programming Voltage on MCLR/VPP/RE3	VDD + 4.0	12.5	V	(Note 2)		
D110A	VIHL	Low-Voltage Programming Voltage on MCLR/VPP/RE3	2.00	5.50	V	(Note 2)		
D111 VDD	Supply Voltage During Programming	2.00	5.50	V	Externally timed, Row Erases and all writes			
			3.0	5.50	V	Self-timed, Bulk Erases only (Note 3)		
D112	IPP	Programming Current on MCLR/VPP/RE3	_	300	μA	(Note 2)		
D113	IDDP	Supply Current During Programming	_	10	mA			
D031	VIL	Input Low Voltage	Vss	0.2 Vdd	V			
D041	Viн	Input High Voltage	0.8 Vdd	Vdd	V			
D080	Vol	Output Low Voltage	_	0.6	V	IOL = 8.5 mA @ 4.5V		
D090	Vон	Output High Voltage	Vdd - 0.7	_	V	IOH = -3.0 mA @ 4.5V		
D012	Сю	Capacitive Loading on I/O pin (PGD)		50	pF	To meet AC specifications		
P1	Tr	MCLR/VPP/RE3 Rise Time to Enter Program/Verify mode	-	1.0	μS	(Notes 1, 2)		
P2 TPGC	TPGC	Serial Clock (PGC) Period	100	_	ns	VDD = 5.0V		
			1		μS	VDD = 2.0V		
P2A TPGCL	TPGCL	Serial Clock (PGC) Low Time	40	_	ns	VDD = 5.0V		
			400	_	ns	VDD = 2.0V		
P2B	TPGCH	Serial Clock (PGC) High Time	40	_	ns	VDD = 5.0V		
			400	_	ns	VDD = 2.0V		
P3	TSET1	Input Data Setup Time to Serial Clock \downarrow	15	—	ns			
P4	THLD1	Input Data Hold Time from PGC \downarrow	15		ns			
P5	TDLY1	Delay Between 4-Bit Command and Command Operand	40	—	ns			
P5A	TDLY1A	Delay Between 4-Bit Command Operand and Next 4-Bit Command	40	_	ns			
P6	TDLY2	Delay Between Last PGC \downarrow of Command Byte to First PGC \uparrow of Read of Data Word	20	_	ns			
P9	TDLY5	PGC High Time (minimum programming time)	1	_	ms	Externally timed		
P10	TDLY6	PGC Low Time After Programming (high-voltage discharge time)	100	—	μS			
P11	TDLY7	Delay to Allow Self-Timed Data Write or Bulk Erase to Occur	5	_	ms			

Note 1: Do not allow excess time when transitioning MCLR between VIL and VIHH. This can cause spurious program executions to occur. The maximum transition time is:

1 TCY + TPWRT (if enabled) + 1024 TOSC (for LP, HS, HS/PLL and XT modes only) +

2 ms (for HS/PLL mode only) + 1.5 μ s (for EC mode only)

where TCY is the instruction cycle time, TPWRT is the Power-up Timer period and TOSC is the oscillator period. For specific values, refer to the Electrical Characteristics section of the device data sheet for the particular device.

2: When ICPRT = 1, this specification also applies to ICVPP.

3: At 0°C-50°C.

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